S/N 09/382182

PATENT

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

Applicant:

HAGIWARA ET AL.

Examiner:

G. GOUDREAU

Serial No.:

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Group Art Unit:

1763

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Title:

METHOD OF FORMING MULTI-LAYER WIRING STRUCTURE

I hereby certify that this paper is being transmitted by facsimile to the U.S. Patent and Trademerk Office on December 6, 2002.

AMENDMENT UNDER RULE 111

Commissioner for Patents Washington, D.C. 20231

Dear Commissioner:

In response to the Official Action dated June 6, 2002, please amend this application as follows:

IN THE CLAIMS

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GROUP 1700

Please cancel claim 3.

Please add claims 9-10 to read as follows:

- A method for forming a multi-layer wiring structure, comprising 9. (New) the following steps:
- (a) etching to form via-holes or wiring gutters through a resist mask on an insulating film between layers of a silica system having a dielectric constant being equal to or less than 3.5, said insulating film between the layers of the silica system containing carbon from 5% by atomic weight to 25% by atomic weight;
- filling up said wiring gutters or said via-holes with conductive material using a (b) damascene method; and